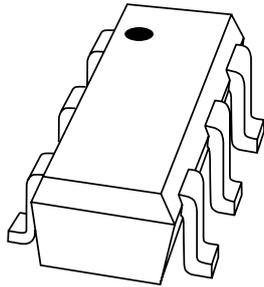


DATA SHEET



BGA2011 900 MHz high linear low noise amplifier

Product specification
Supersedes data of 2000 Sep 06

2000 Dec 04

900 MHz high linear low noise amplifier

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FEATURES

- Low current, low voltage
- High linearity
- High power gain
- Low noise
- Integrated temperature compensated biasing
- Control pin for adjustment bias current.

APPLICATIONS

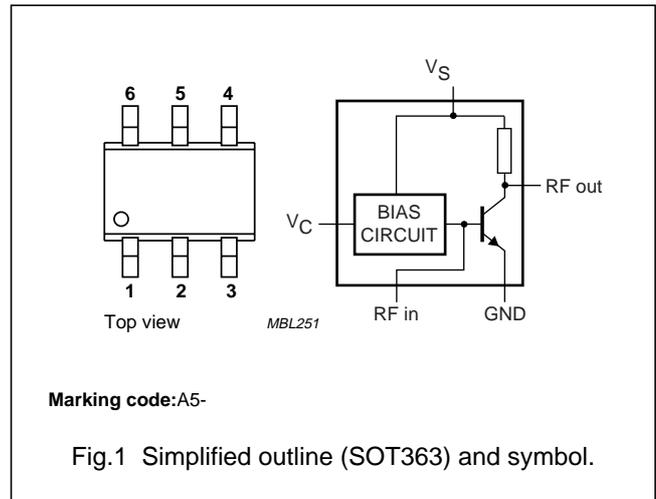
- RF front end
- Low noise amplifiers, e.g. CDMA, PHs, Dect, etc.

DESCRIPTION

Silicon Monolithic Microwave Integrated Circuit (MMIC) amplifier consisting of an NPN double polysilicon transistor with integrated biasing for low voltage applications in a 6-pin SOT363 plastic SMD package.

PINNING

PIN	DESCRIPTION
1	RF in
2	V _C
3	V _S
4	RF out
5, 6	GND



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V _S	DC supply voltage	RF input AC coupled	3	4.5	V
I _S	DC supply current		15	–	mA
I _C	DC control current	V _C = V _S	0.11	–	mA
S ₂₁ ²	insertion power gain	in application circuit, see Fig.2; f = 900 MHz	19	–	dB
NF	noise figure	I _S = 15 mA; f = 900 MHz	1.7	–	dB

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _S	DC supply voltage	RF input AC coupled	–	4.5	V
V _C	voltage on control pin		–	V _S	V
I _S	supply current	forced by DC voltage on RF input	–	30	mA
I _C	control current		–	0.25	mA
P _{tot}	total power dissipation	T _s ≤ 100 °C	–	135	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	operating junction temperature		–	150	°C

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-s}$	thermal resistance from junction to solder point	$P_{tot} = 135\text{ mW}$; $T_s \leq 100\text{ }^\circ\text{C}$	350	K/W

CHARACTERISTICS

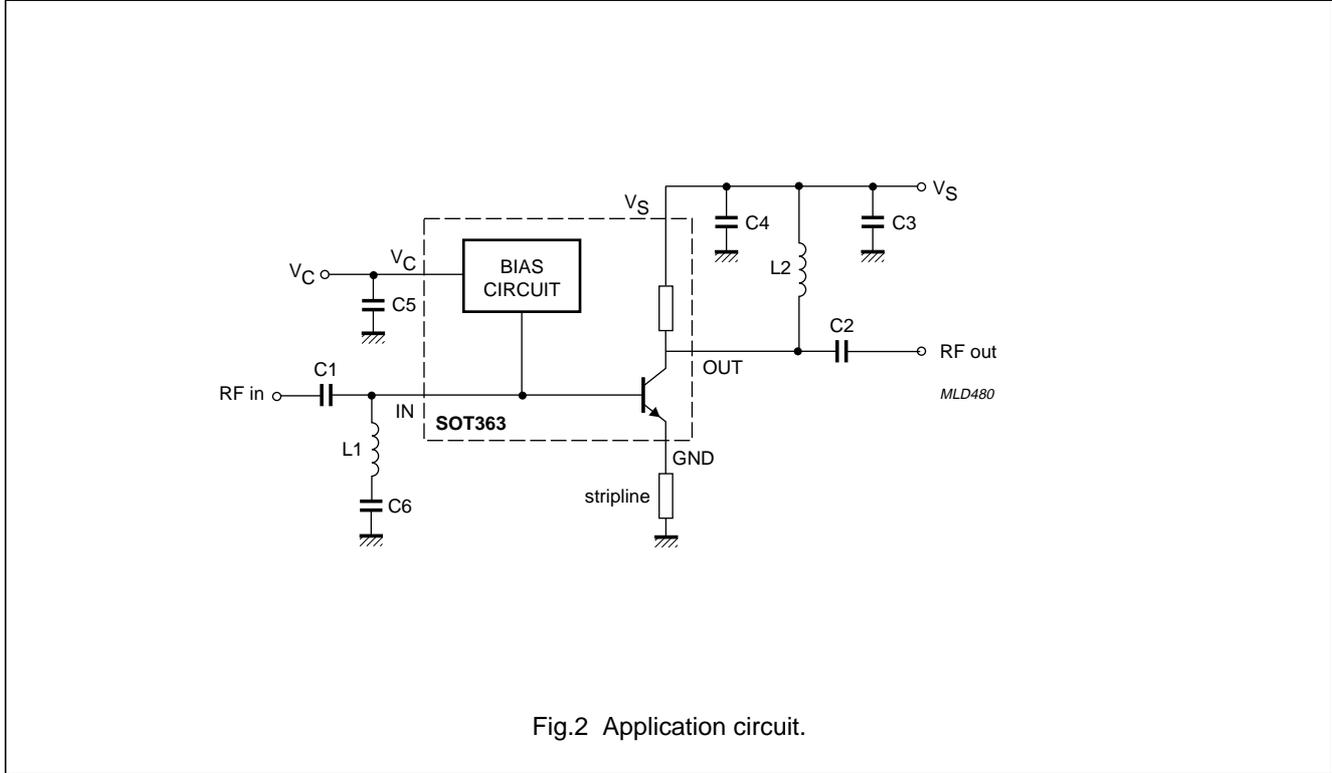
RF input AC coupled; $V_S = 3\text{ V}$; $I_S = 15\text{ mA}$; $f = 900\text{ MHz}$; $T_j = 25\text{ }^\circ\text{C}$; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_S	supply current		10	15	20	mA
I_C	control current		–	0.11	–	mA
$R_{L\ IN}$	return losses input	typical application; see Fig.2	–	–11	–	dB
		high IP3 (see Fig.2; stripline = 0 mm)	–	–11	–	dB
		high IP3 (see Fig.2; stripline = 1.5 mm)	–	–17	–	dB
$R_{L\ OUT}$	return losses output	typical application; see Fig.2	–	–11	–	dB
		high IP3 (see Fig.2; stripline = 0 mm)	–	–12	–	dB
		high IP3 (see Fig.2; stripline = 1.5 mm)	–	–14	–	dB
$ S_{21} ^2$	insertion power gain	typical application; see Fig.2	–	15	–	dB
		high IP3 (see Fig.2; stripline = 0 mm)	–	19	–	dB
		high IP3 (see Fig.2; stripline = 1.5 mm)	–	16	–	dB
NF	noise figure	typical application; see Fig.2; $I_S = 15\text{ mA}$	–	1.5	–	dB
		high IP3 (see Fig.2; stripline = 0 mm)	–	1.6	–	dB
		high IP3 (see Fig.2; stripline = 1.5 mm)	–	1.7	–	dB
$IP3_{in}$	input intercept point	typical application; see Fig.2	–	–2	–	dBm
		high IP3 (see Fig.2; stripline = 0 mm)	–	4	–	dBm
		high IP3 (see Fig.2; stripline = 1.5 mm)	–	10	–	dBm

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APPLICATION INFORMATION



List of components (see Fig.2)

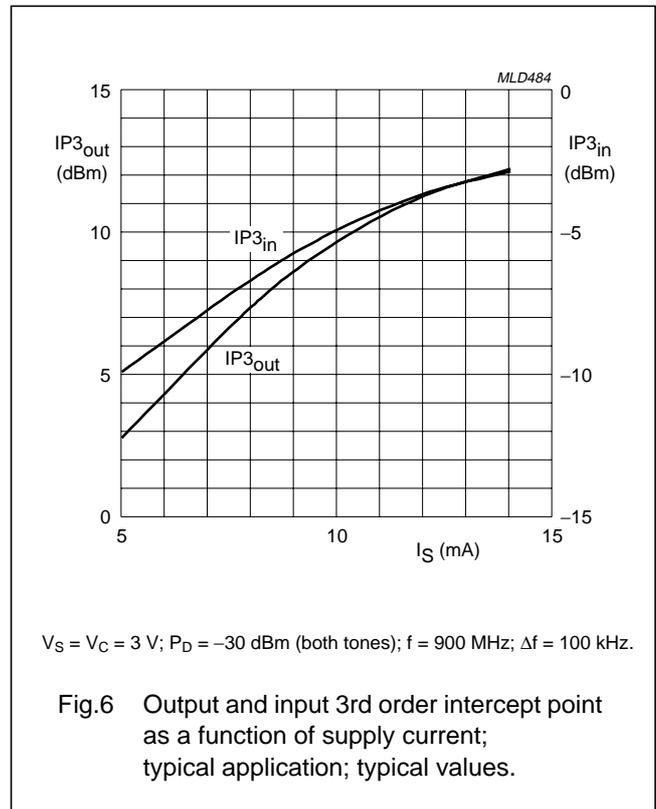
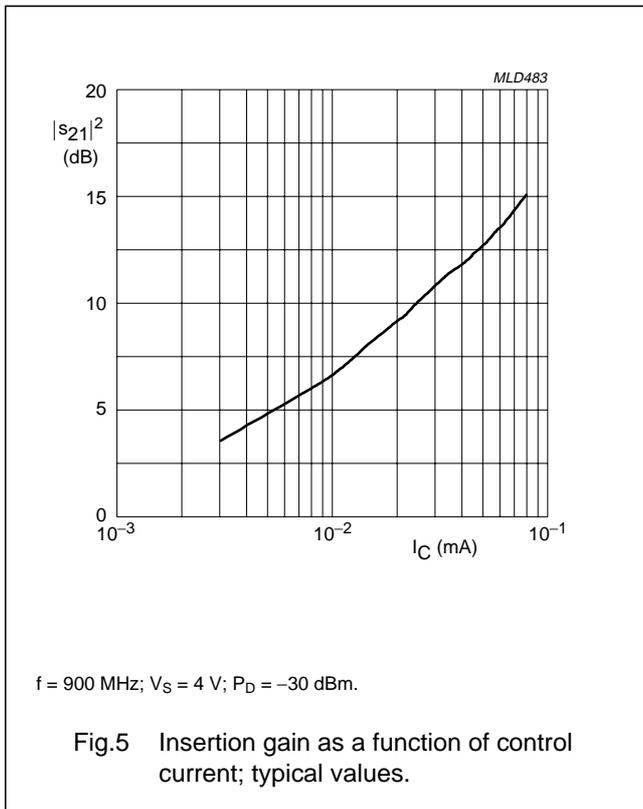
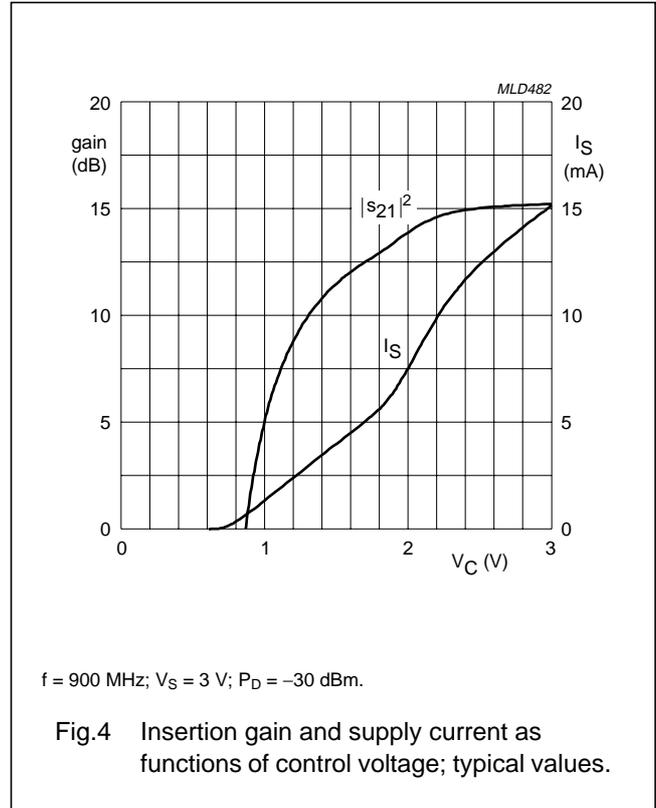
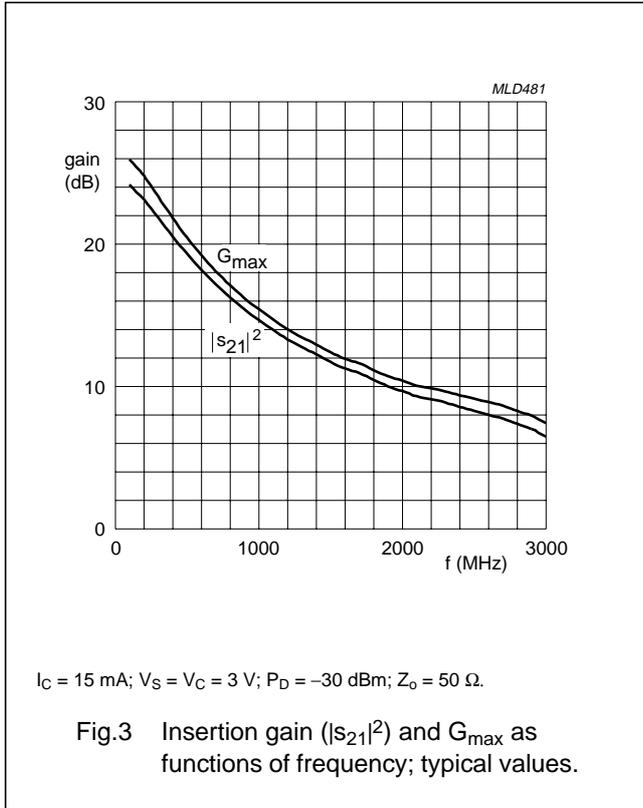
COMPONENT	DESCRIPTION	TYPICAL APPLICATION	HIGH IP3 APPLICATION	DIMENSIONS
C1, C2	multilayer ceramic chip capacitor	100 pF	100 pF	0603
C3, C5	multilayer ceramic chip capacitor	22 nF	22 nF	0603
C4	multilayer ceramic chip capacitor	5.6 pF	5.6 pF	0603
C6	multilayer ceramic chip capacitor	–	2 x 100 nF	0805
L1	SMD inductor	–	10 nH	0603
L2	SMD inductor	–	8.2 nH	0603

Note

- The stripline (w = 0.7 mm) is on a gold plated double copper-clad printed-circuit board ($\epsilon_r = 6.15$), board thickness = 0.64 mm, copper thickness = 35 μm , gold thickness = 5 μm .

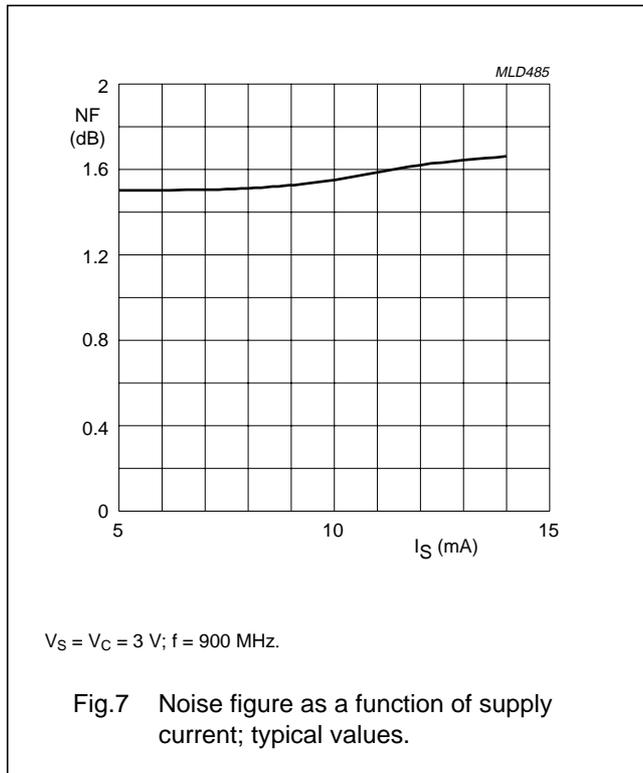
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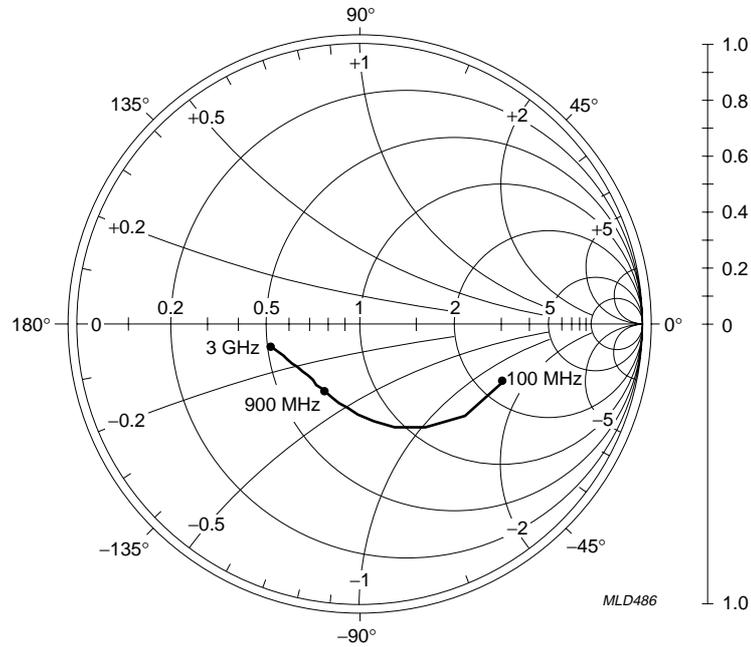
Scattering parameters

$V_S = V_C = 3\text{ V}; P_D = -30\text{ dBm}; Z_0 = 50\ \Omega; T_{amb} = 25\text{ }^\circ\text{C}$

f (MHz)	S ₁₁		S ₂₁		S ₁₂		S ₂₂	
	MAGNITUDE (ratio)	ANGLE (deg)						
100	0.553	-22.45	16.198	160.5	0.006	76.72	0.115	-87.98
200	0.499	-42.12	14.354	145.4	0.012	67.53	0.184	-113.5
400	0.394	-71.44	10.688	124.6	0.018	59.55	0.256	-141.2
600	0.331	-90.58	8.156	112.2	0.021	58.29	0.283	-158.1
800	0.295	-104.0	6.512	103.9	0.024	60.91	0.293	-170.5
1000	0.276	-114.9	5.415	97.72	0.027	64.65	0.298	178.7
1200	0.267	-124.2	4.640	93.01	0.032	69.04	0.304	169.5
1400	0.262	-134.2	4.112	89.10	0.037	73.22	0.310	162.5
1600	0.270	-144.2	3.659	85.21	0.043	75.43	0.311	157.0
1800	0.287	-152.7	3.336	82.21	0.049	77.84	0.309	152.7
2000	0.309	-159.7	3.045	78.21	0.057	78.60	0.312	150.5
2200	0.339	-166.2	2.849	73.94	0.066	77.96	0.304	149.6
2400	0.360	-172.0	2.680	69.19	0.076	75.04	0.291	151.4
2600	0.390	-175.9	2.511	64.60	0.086	74.92	0.292	149.2
2800	0.398	178.0	2.332	59.20	0.094	69.95	0.278	148.4
3000	0.392	173.9	2.108	56.72	0.099	69.12	0.317	140.0

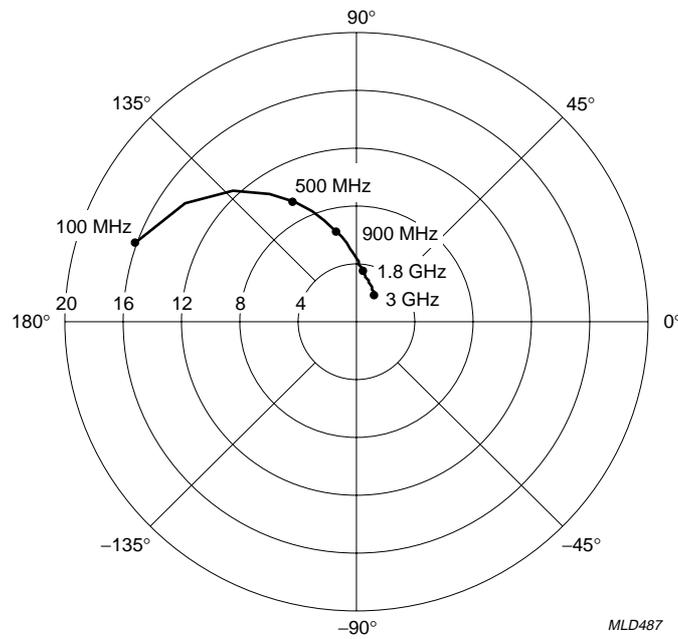
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$I_C = 15 \text{ mA}$; $V_S = V_C = 3 \text{ V}$; $P_D = -30 \text{ dBm}$; $Z_0 = 50 \Omega$.

Fig.8 Common emitter input reflection coefficient (s_{11}); typical values.

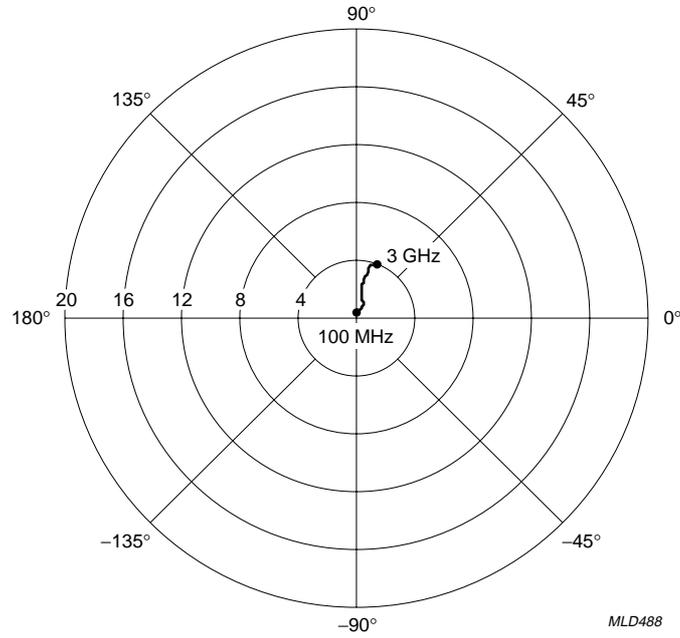


$I_C = 15 \text{ mA}$; $V_S = V_C = 3 \text{ V}$; $P_D = -30 \text{ dBm}$; $Z_0 = 50 \Omega$.

Fig.9 Common emitter forward transmission coefficient (s_{21}); typical values.

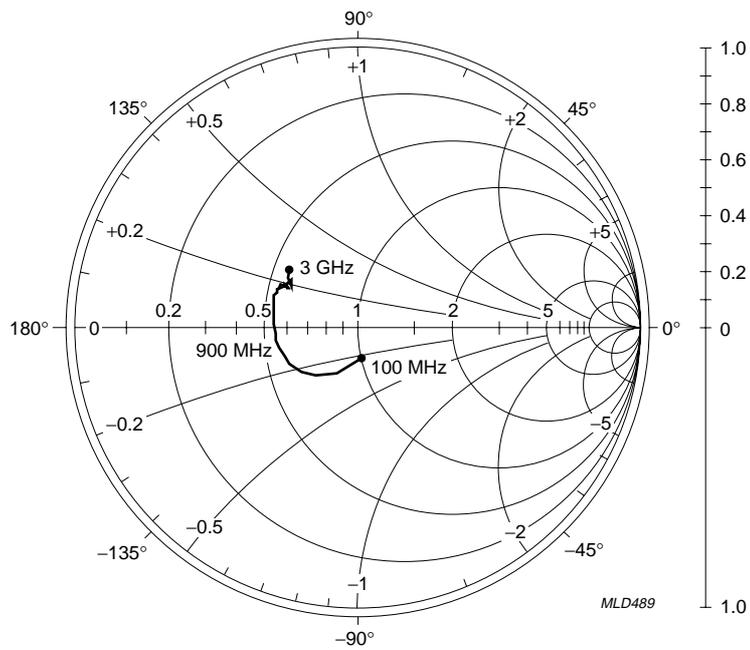
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$I_C = 15 \text{ mA}$; $V_S = V_C = 3 \text{ V}$; $P_D = -30 \text{ dBm}$; $Z_0 = 50 \Omega$.

Fig.10 Common emitter reverse transmission coefficient (s_{12}); typical values.



$I_C = 15 \text{ mA}$; $V_S = V_C = 3 \text{ V}$; $P_D = -30 \text{ dBm}$; $Z_0 = 50 \Omega$.

Fig.11 Common emitter output reflection coefficient (s_{22}); typical values.

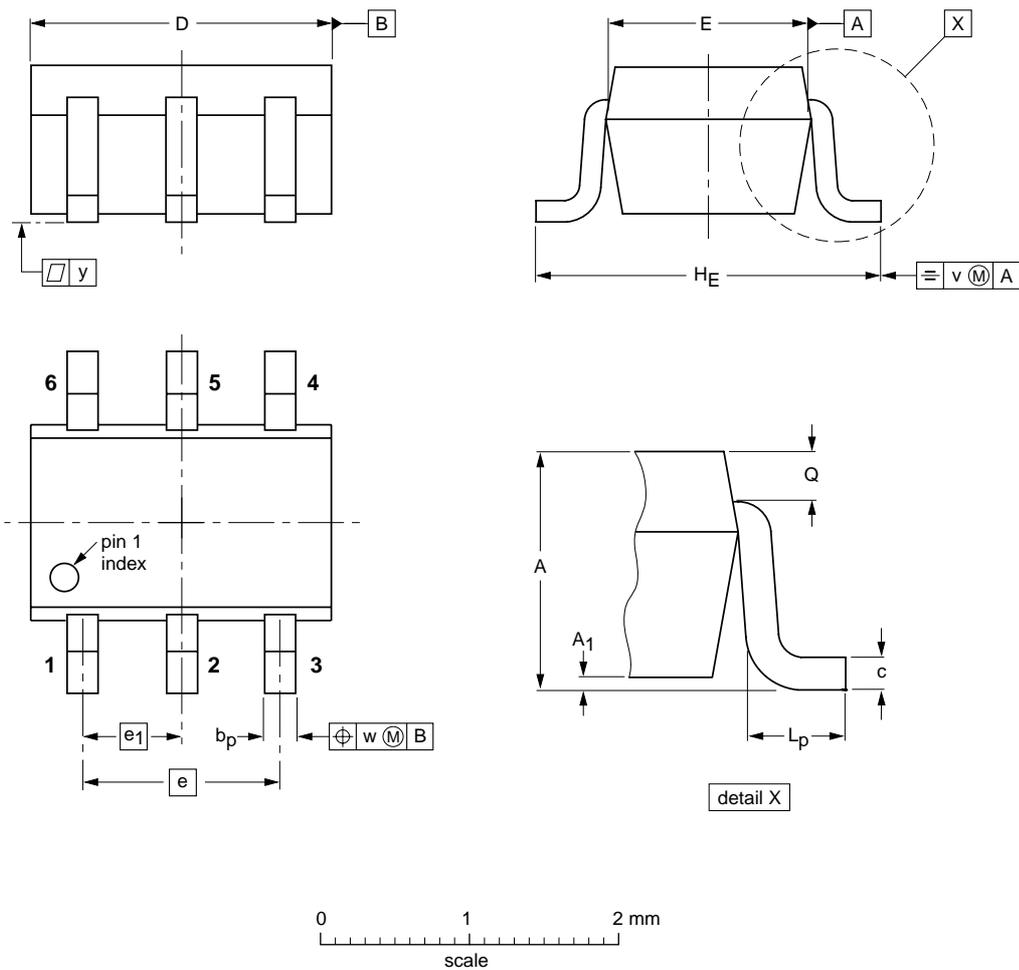
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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT363



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT363			SC-88			97-02-28

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DATA SHEET STATUS

DATA SHEET STATUS	PRODUCT STATUS	DEFINITIONS ⁽¹⁾
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.
Preliminary specification	Qualification	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.
Product specification	Production	This data sheet contains final specifications. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.

Note

1. Please consult the most recently issued data sheet before initiating or completing a design.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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